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**1N4150**

## Features

- Lead Free Finish/Rohs Compliant (Note1)
- Low Current Leakage
- Compression Bond Construction
- Low Cost
- Marking : Cathode band and type number
- Moisture Sensitivity Level 1

## Maximum Ratings

- Operating Temperature: -55°C to +150°C
- Storage Temperature: -55°C to +150°C
- Maximum Thermal Resistance; 300°C/W Junction To Ambient

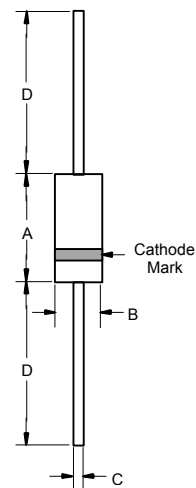
## Electrical Characteristics @ 25°C Unless Otherwise Specified

Reverse Voltage	$V_R$	50V	
Breakdown Voltage	$B_V$	75V	$I_R=5.0 \mu A$
Average Rectified Current	$I_O$	200mA	
Power Dissipation	$P_{TOT}$	500mW	
Peak Forward Surge Current	$I_{FSM}$	1.0A 4.0A	Pulse Width=1.0S Pulse Width=1.0μS
Maximum Instantaneous Forward Voltage	$V_F$	1.0V	$I_{FM} = 100mA;$ $T_J = 25^\circ C^*$
Maximum DC Reverse Current At Rated DC Blocking Voltage	$I_R$	100nA 100μA	$V_R=50Volts$ $T_J = 25^\circ C$ $T_J = 150^\circ C$
Maximum Junction Capacitance	$C_J$	2.5pF	Measured at 1.0MHz, $V_R=0$
Maximum Reverse Recovery Time	$T_{rr}$	4.0nS	$I_F=10mA$ $V_R=6.0V$ $R_L=100\Omega$

Note: 1. Lead in Glass Exemption Applied, see EU Directive Annex 5.

**500mW 75 Volt Silicon Epitaxial Diode**

**DO-35**



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	---	.166	---	4.2	
B	---	.079	---	2.00	
C	---	.020	---	.52	
D	1.000	---	25.40	---	